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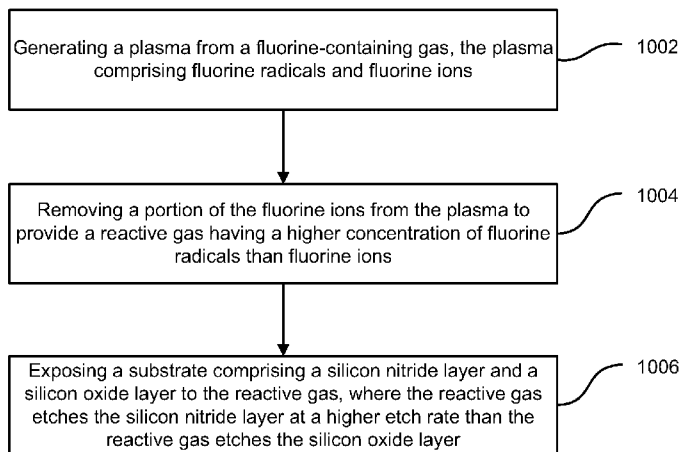
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[Continued on next page]

(54) **Title:** METHODS FOR ETCH OF SIN FILMS



(57) **Abstract:** A method of selectively etching silicon nitride from a substrate comprising a silicon nitride layer and a silicon oxide layer includes flowing a fluorine-containing gas into a plasma generation region of a substrate processing chamber and applying energy to the fluorine-containing gas to generate a plasma in the plasma generation region. The plasma comprises fluorine radicals and fluorine ions. The method also includes filtering the plasma to provide a reactive gas having a higher concentration of fluorine radicals than fluorine ions and flowing the reactive gas into a gas reaction region of the substrate processing chamber. The method also includes exposing the substrate to the reactive gas in the gas reaction region of the substrate processing chamber. The reactive gas etches the silicon nitride layer at a higher etch rate than the reactive gas etches the silicon oxide layer.

FIG. 10

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A. CLASSIFICATION OF SUBJECT MATTER**H01L 21/3065(2006.01)i, H01L 21/318(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L 21/3065; G06F 19/00; H01L 21/30; B44C 1/22

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords:silicon, oxide, etching, nitride, fluorine, gas, plasma, filtering, reactive, ion, radical.

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2002-0045966 A1 (HEE-TAE LEE et al.) 18 April 2002 See abstract, paragraphs [0033]-[0036],[0050], claims 1-5,15 and figure 2.	1-15
A	US 2009-0104782 A1 (XINLAING LU et al.) 23 April 2009 See abstract, paragraphs [0021]-[0031], claims 1,7,10 and figure 1.	1-15
A	US 2011-0008950 A1 (ZHI XU) 13 January 2011 See abstract, paragraphs [0010]-[0013],[0037]-[0043], claims 1,16 and figures 1,4.	1-15
A	US 2009-0045167 A1 (KOJI MARUYAMA) 19 February 2009 See abstract, paragraphs [0044],[0045] and claims 1,5.	1-15

 Further documents are listed in the continuation of Box C. See patent family annex.

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"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

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"&" document member of the same patent family

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INTERNATIONAL SEARCH REPORT

Information on patent family members

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